

Abstract of the Disclosure:

The IGBT (insulated gate bipolar transistor) has a weakly doped drift zone of a first conductivity formed in a weakly doped semiconductor substrate of the same conductivity. A

- 5 highly doped first well zone of the first conductivity and a highly doped second well zone of a second conductivity are arranged between the drift zone and the semiconductor substrate.

09931E89.084604
T09T80"689T8660

WHS:tk-MUH-11086F//8/10/2001